

ABSTRACT

The process for programming a set of memory cells is improved by adapting the programming process based on behavior of the memory cells. For example, a set of program pulses is applied to the word line for a set of flash memory cells. A
5 determination is made as to which memory cells are easier to program and which memory cells are harder to program. Bit line voltages (or other parameters) can be adjusted based on the determination of which memory cells are easier to program and which memory cells are harder to program. The programming process will then continue with the adjusted bit line voltages (or other parameters).